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PTO/SB/08A (10/01) (Substitute for form 1449A/PTO)	ATTY. DOCKET NO. UMC-96-279 CON 2 Client/Matter No. 81848.0016.002	APPLICATION NO.: 09/991,196
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) Sheet <u> 1 </u> of <u> 3 </u>	FIRST NAMED INVENTOR: CHIH-CHIEN LIU et al.	
	FILING DATE November 20, 2001	ART UNIT 1711

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						YES	NO

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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